

# FCP380N60E / FCPF380N60E

## N-Channel SuperFET® II MOSFET

600 V, 10.2 A, 380 mΩ

### Features

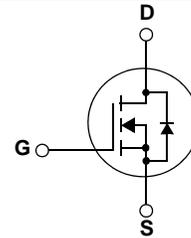
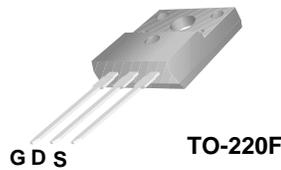
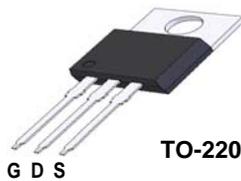
- 650 V @  $T_J = 150^\circ\text{C}$
- Max.  $R_{DS(on)} = 380\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 34\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss,eff} = 97\text{ pF}$ )
- 100% Avalanche Tested

### Applications

- LCD / LED / PDP TV Lighting
- Solar Inverter
- AC-DC Power Supply

### Description

SuperFET®II MOSFET is Fairchild Semiconductor®'s first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFETII MOSFET is suitable for various AC/DC power conversion for system miniaturization and higher efficiency.



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FCP380N60E	FCPF380N60E	Unit
$V_{DSS}$	Drain to Source Voltage	600		V
$V_{GSS}$	Gate to Source Voltage	- DC	$\pm 20$	V
		- AC ( $f > 1\text{ Hz}$ )	$\pm 30$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	10.2	10.2*
		- Continuous ( $T_C = 100^\circ\text{C}$ )	6.4	6.4*
$I_{DM}$	Drain Current	- Pulsed (Note 1)	30.6	30.6*
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	211.6		mJ
$I_{AR}$	Avalanche Current (Note 1)	2.3		A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	1.06		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	20		V/ns
	MOSFET dv/dt	100		
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	106	31
		- Derate above $25^\circ\text{C}$	0.85	0.25
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

\*Drain current limited by maximum junction temperature

### Thermal Characteristics

Symbol	Parameter	FCP380N60E	FCPF380N60E	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.18	4	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink (Typical)	0.5	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	62.5	

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCP380N60E	FCP380N60E	TO-220	-	-	50
FCPF380N60E	FCPF380N60E	TO-220F	-	-	50

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 25^\circ\text{C}$	600	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 150^\circ\text{C}$	650	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$	-	0.67	-	$\text{V}/^\circ\text{C}$
$BV_{DS}$	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ A}$	-	700	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	-	-	10	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.5	-	3.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	-	0.32	0.38	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 5\text{ A}$	-	10	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$	-	1330	1770	pF
$C_{oss}$	Output Capacitance		-	945	1260	pF
$C_{rss}$	Reverse Transfer Capacitance		-	60	90	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	-	25	-	pF
$C_{oss\text{ eff.}}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	-	97	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}, I_D = 5\text{ A}$ $V_{GS} = 10\text{ V}$	-	34	45	nC
$Q_{gs}$	Gate to Source Gate Charge		-	5.3	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		(Note 4)	-	13	-
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	6	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 5\text{ A}$ $V_{GS} = 10\text{ V}, R_G = 4.7\text{ }\Omega$	-	17	44	ns
$t_r$	Turn-On Rise Time		-	9	28	ns
$t_{d(off)}$	Turn-Off Delay Time		-	64	138	ns
$t_f$	Turn-Off Fall Time		(Note 4)	-	10	30

### Drain-Source Diode Characteristics

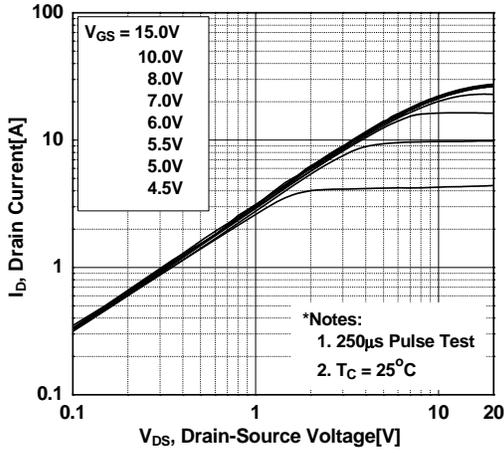
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	10.2	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	30.6	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 5\text{ A}$	-	-	1.2	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_{SD} = 5\text{ A}$	-	240	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100\text{ A}/\mu\text{s}$	-	3	-	$\mu\text{C}$

#### Notes:

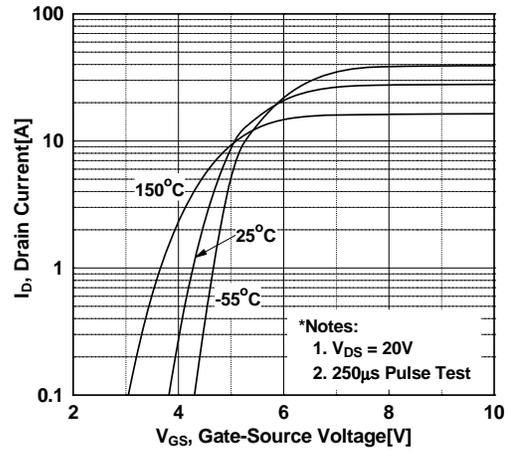
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 2.3\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 5.1\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

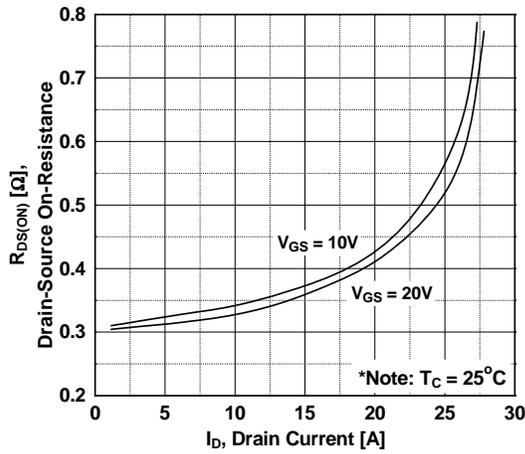
**Figure 1. On-Region Characteristics**



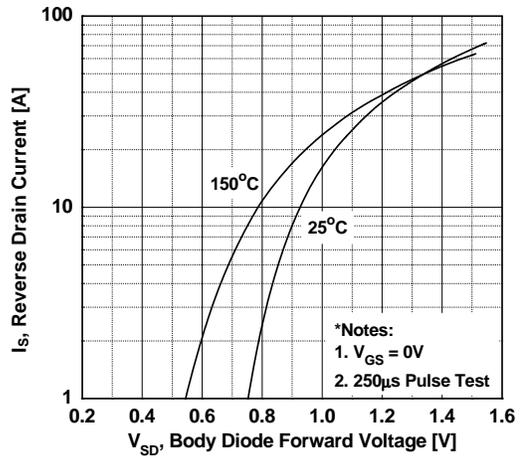
**Figure 2. Transfer Characteristics**



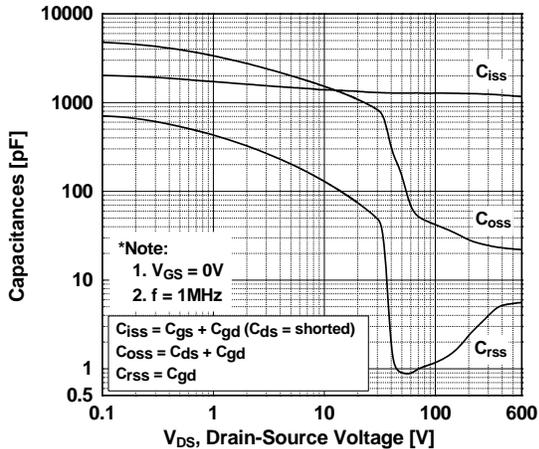
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



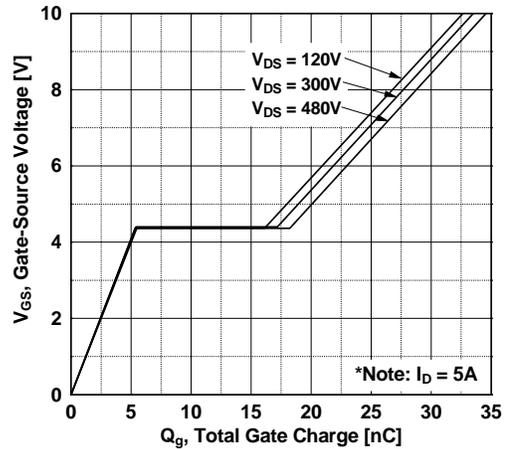
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

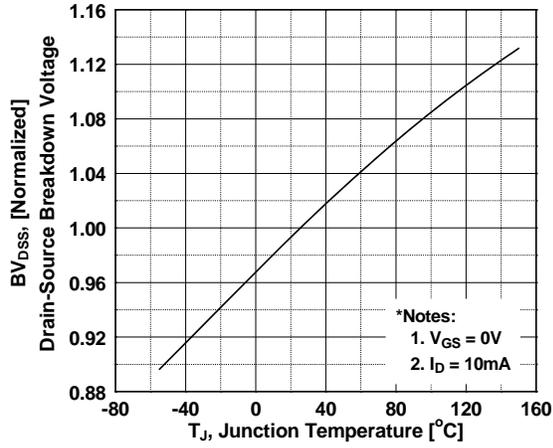


**Figure 6. Gate Charge Characteristics**

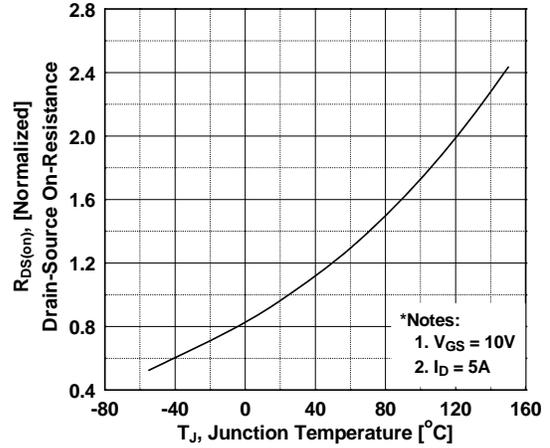


**Typical Performance Characteristics** (Continued)

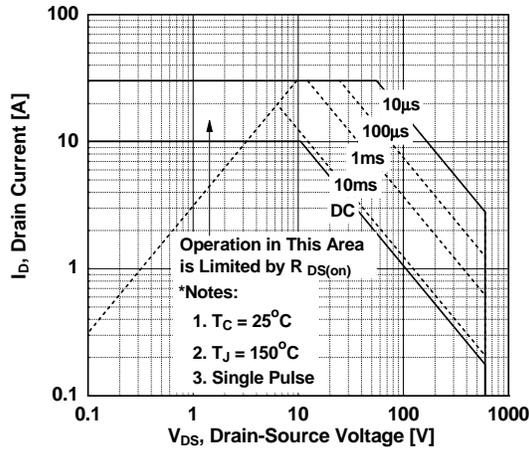
**Figure 7. Breakdown Voltage Variation vs. Temperature**



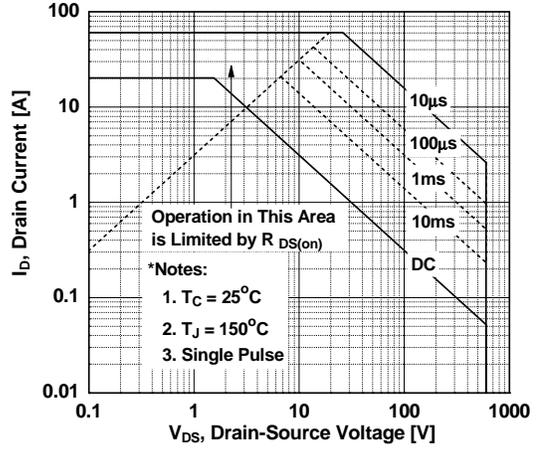
**Figure 8. On-Resistance Variation vs. Temperature**



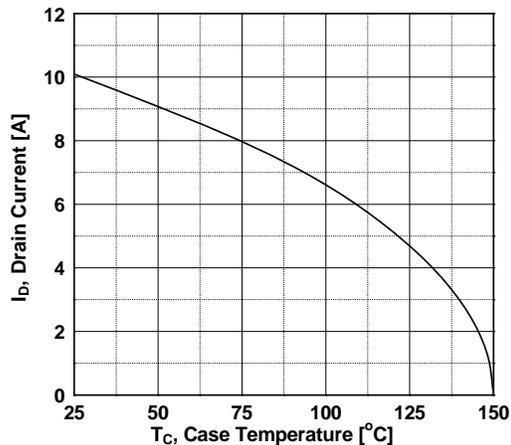
**Figure 9. Maximum Safe Operating Area vs. Case Temperature - FCP380N60E**



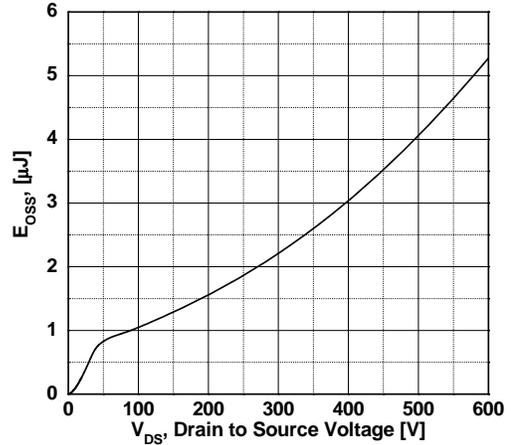
**Figure 10. Maximum Safe Operating Area vs. Case Temperature - FCPF380N60E**



**Figure 11. Maximum Drain Current**



**Figure 12. E\_oss vs. Drain to Source Voltage Switching Capability**



Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve - FCP380N60E

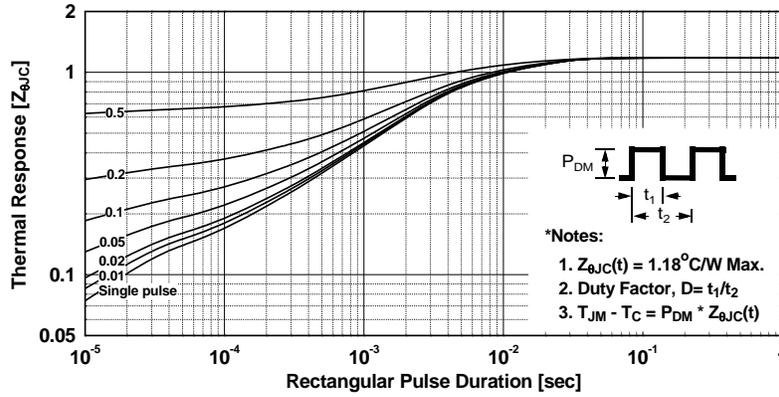
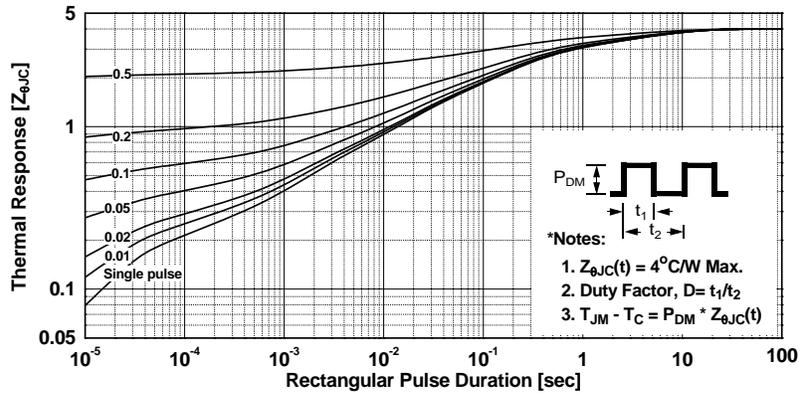
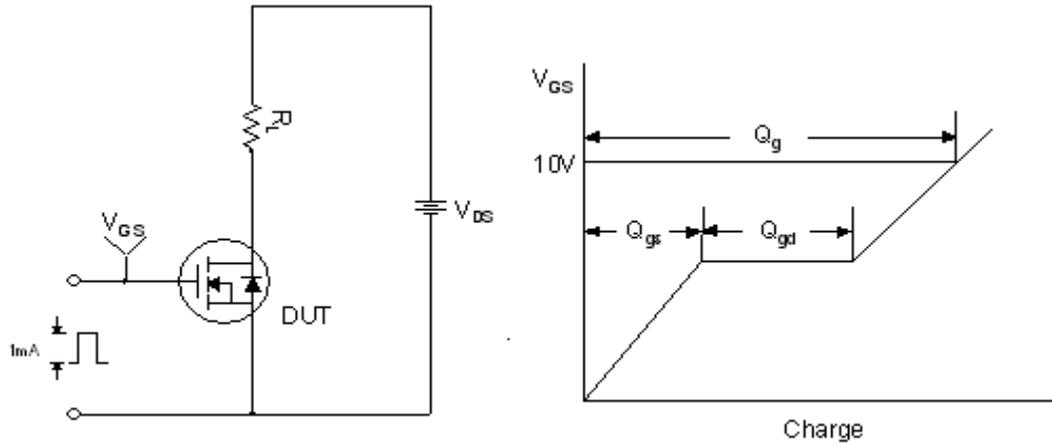


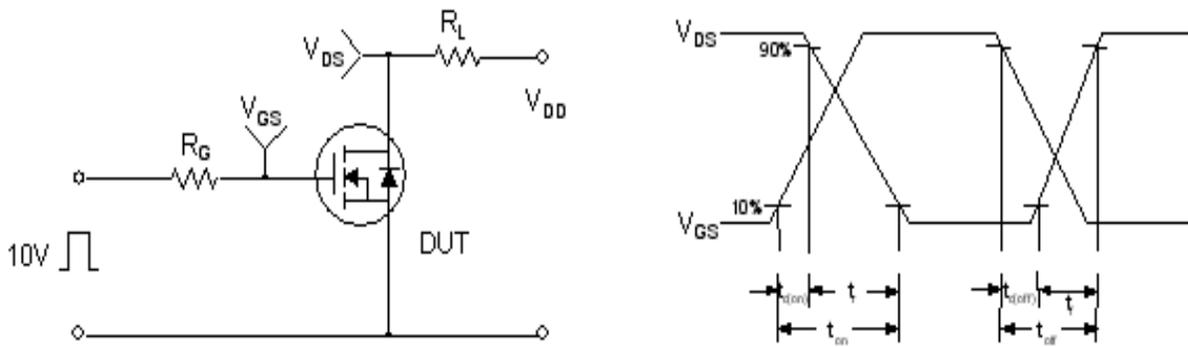
Figure 14. Transient Thermal Response Curve - FCPF380N60E



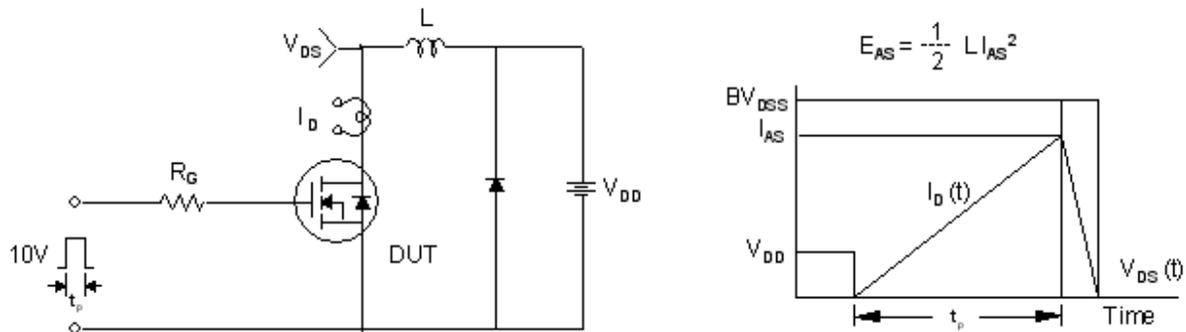
**Gate Charge Test Circuit & Waveform**



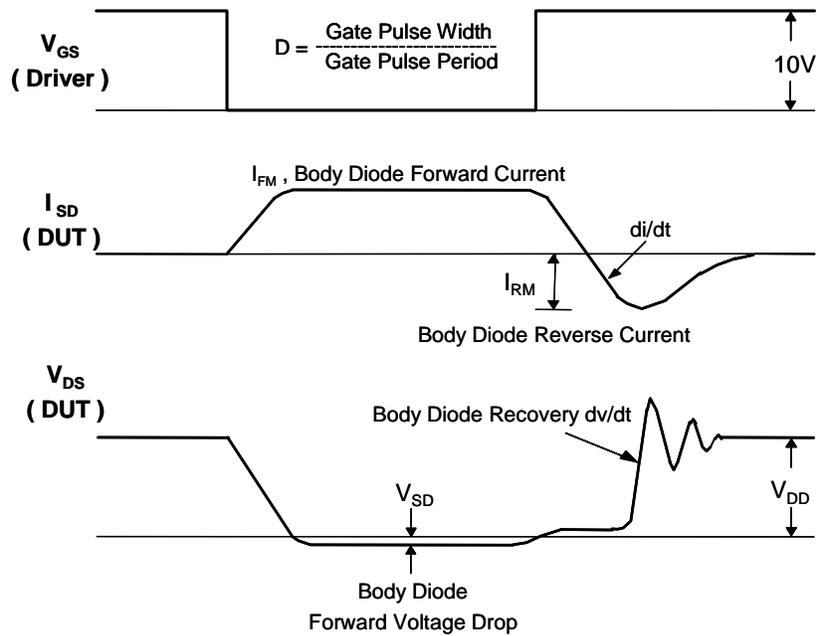
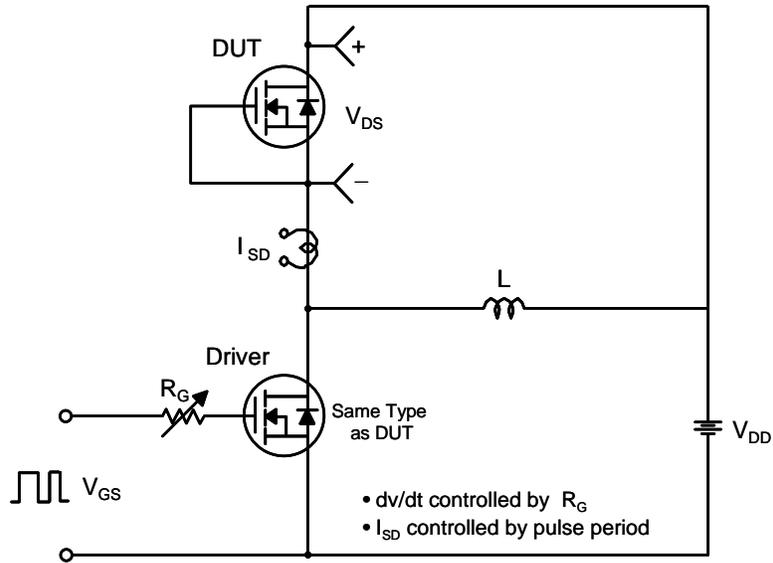
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

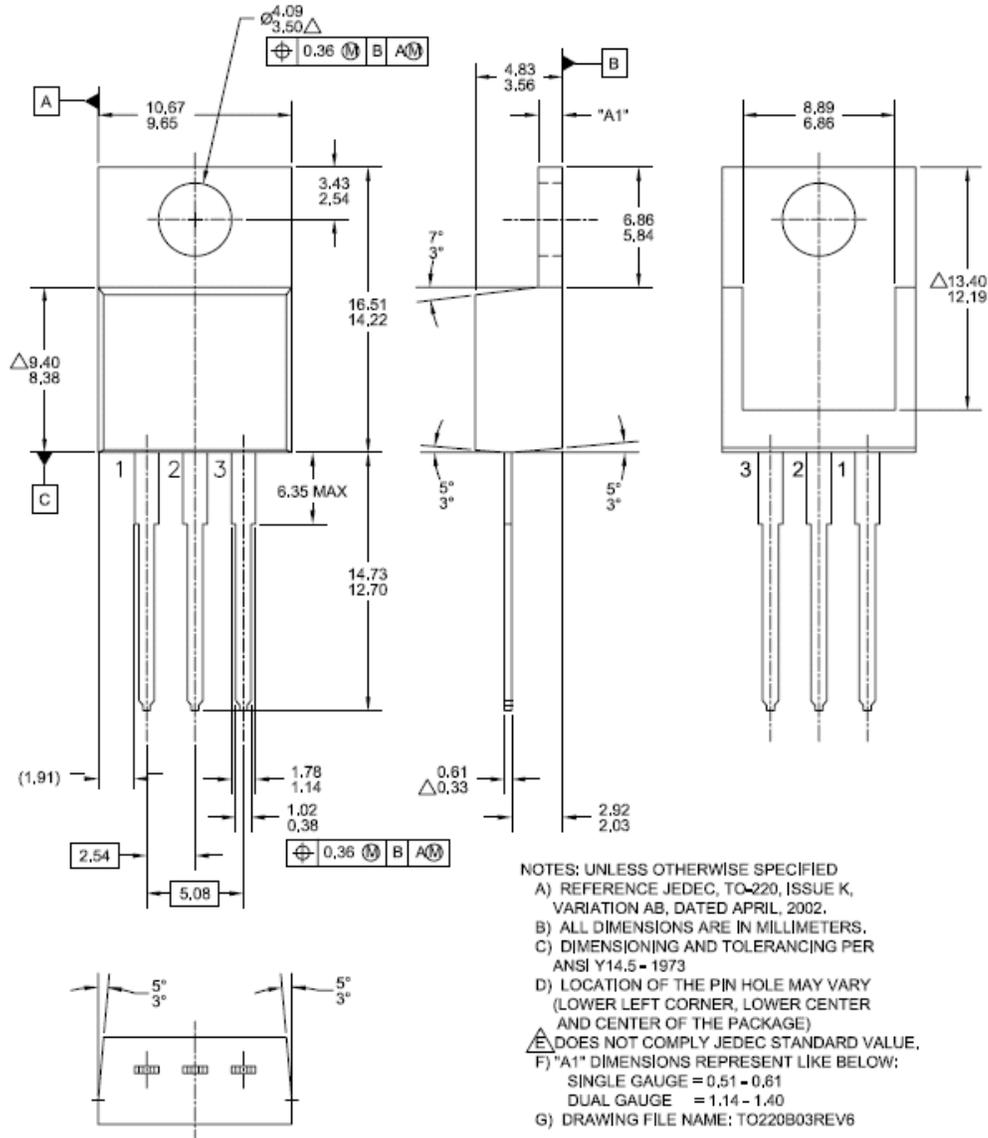


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-220AB







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|                          | QS™   |                  |
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